

## General Description

The WSP4430 is the highest performance trench N-Channel MOSFET with extreme high cell density, which provide excellent  $R_{DS(ON)}$  and gate charge for most of the synchronous buck converter applications.

The WSP4430 meet the RoHS and Green Product requirement, 100%  $E_{AS}$  guaranteed with full function reliability approved.

## Features

- 100% UIS Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

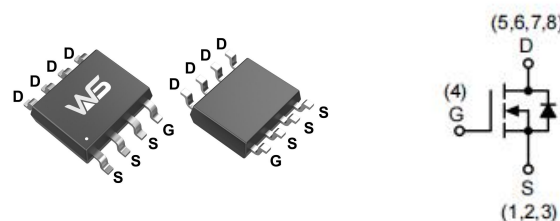
## Product Summary

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
30V	4.2mΩ	20A

## Applications

- Power Management for Industrial DC/DC Converters
- Uninterruptible power supply

## SOP-8L Pin Configuration



## Absolute Maximum Ratings ( $T_A=25^{\circ}\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
$V_{DS}$	Drain-Source Voltage		30	V
$V_{GS}$	Gate-Source Voltage		$\pm 20$	
$I_D$ <sup>7</sup>	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	20	A
		$T_C=100^{\circ}\text{C}$	15	
$I_{DM}$ <sup>3</sup>	Pulse Drain Current		70	W
$P_D$ <sup>2</sup>	Power Dissipation	$T_C=25^{\circ}\text{C}$	3.5	
$I_{AS}$ <sup>3</sup>	Single pulse Avalanche Current		34	A
$E_{AS}$ <sup>3</sup>	Single pulse Avalanche Energy	$L=0.3\text{mH}$	110	mJ
$T_{STG}$	Storage Temperature Range		-55 to 150	$^{\circ}\text{C}$
$T_J$	Operating Junction Temperature Range		-55 to 150	
$R_{\theta JA}$ <sup>1,4</sup>	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	21	$^{\circ}\text{C/W}$
		Steady State	65	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		36	

## Electrical Characteristics ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$	---	4.2	5.5	m $\Omega$
		$V_{GS}=4.5V, I_D=20A$	---	5.6	7.3	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.5	2.2	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=40V, V_{GS}=0V$	---	---	1.0	$\mu A$
		$T_J=55^\circ C$	---	---	5.0	
$I_{GSS}$	Gate-Source Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=20A$	---	20	---	S
$R_G$	Gate Resistance	$f=1.0MHz$	1.0	2.0	3.1	$\Omega$
$Q_g$	Total Gate Charge (10V)	$V_{DS}=20V, V_{GS}=10V, I_D=20A$	---	33	---	nC
$Q_g$	Total Gate Charge (4.5V)		---	19	---	
$Q_{gs}$	Gate-Source Charge		---	5.5	---	
$Q_{gd}$	Gate-Drain Charge		---	7.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=20V, V_{GS}=10V, R_L=1\Omega, R_{GEN}=3\Omega$	---	9	---	ns
$T_r$	Rise Time		---	8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	28	---	
$T_f$	Fall Time		---	5	---	
$C_{iss}$	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1.0MHz$	---	1460	---	pF
$C_{oss}$	Output Capacitance		---	210	---	
$C_{rss}$	Reverse Transfer Capacitance		---	187	---	

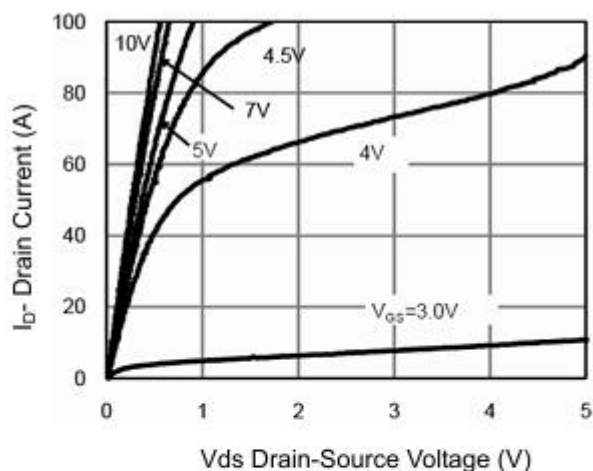
## Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
$I_S$	Continuous Source Current		---	---	20	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=1A$	---	0.7	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=20A, di/dt=500A/\mu s$	---	27	---	ns
$Q_{rr}$	Reverse Recovery Charge		---	20	---	nC

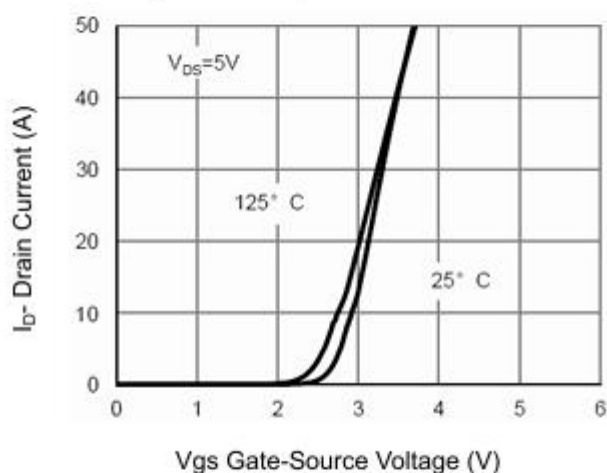
### Note:

- The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ C$ . The Power dissipation  $P_{DSM}$  is based on  $R_{\theta JA} \leq 10s$  and the maximum allowed junction temperature of  $150^\circ C$ . The value in any given application depends on the user's specific board design.
- The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^\circ C$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- Single pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ C$ .
- The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case  $R_{\theta JC}$  and case to ambient.
- The static characteristics in Figures 1 to 6 are obtained using  $<300\mu s$  pulses, duty cycle 0.5% max.
- These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_{J(MAX)}=150^\circ C$ . The SOA curve provides a single pulse rating.
- The maximum current rating is package limited.
- These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ C$ .
- The maximum current rating is silicon limited

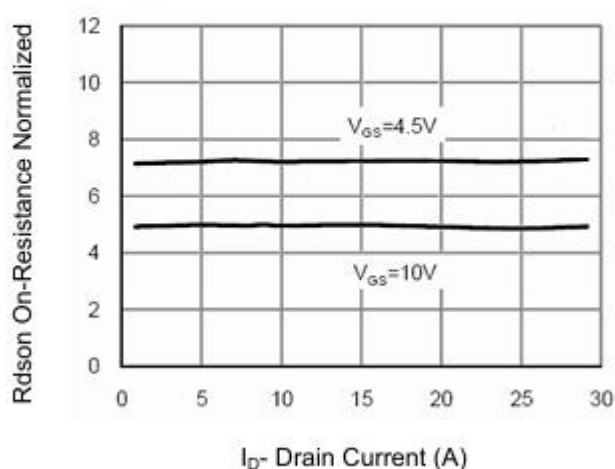
## Typical Characteristics



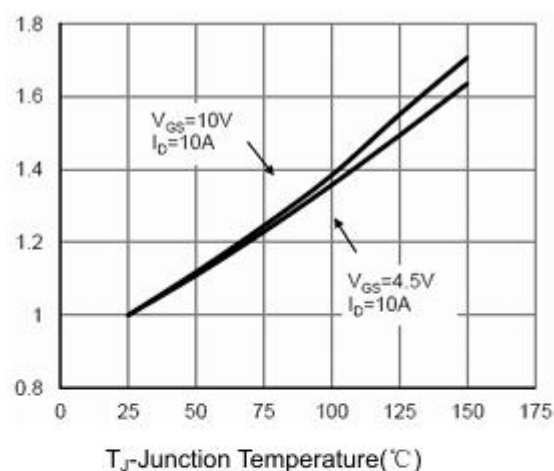
**Figure 1 Output Characteristics**



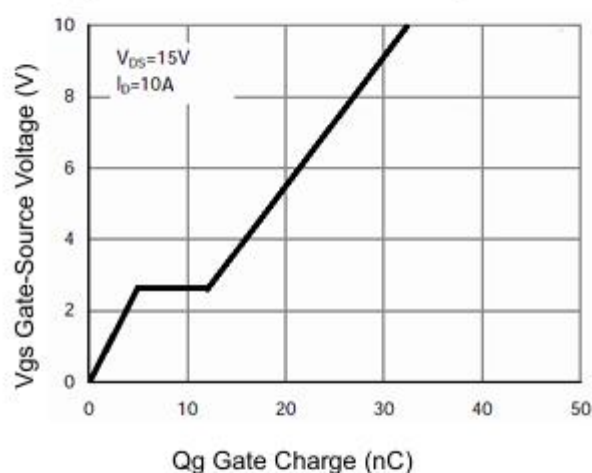
**Figure 2 Transfer Characteristics**



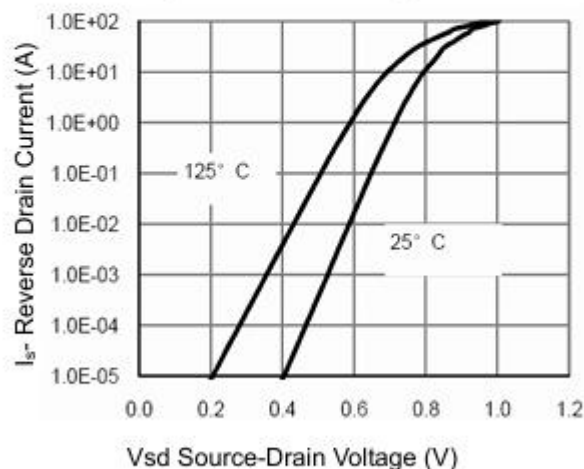
**Figure 3 Rdson- Drain Current**



**Figure 4 Rdson-Junction Temperature**

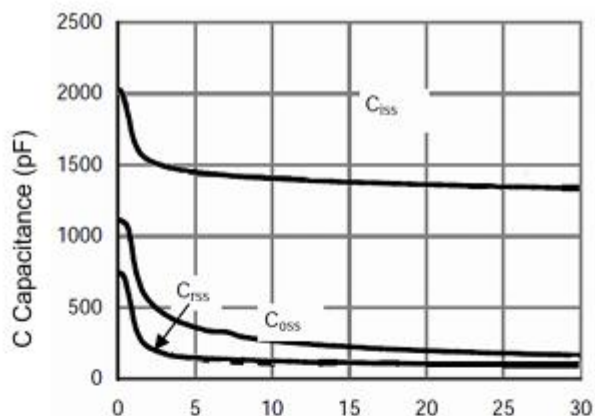


**Figure 5 Gate Charge**

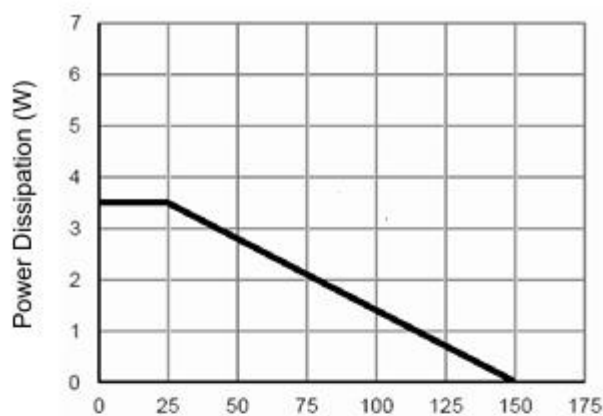


**Figure 6 Source- Drain Diode Forward**

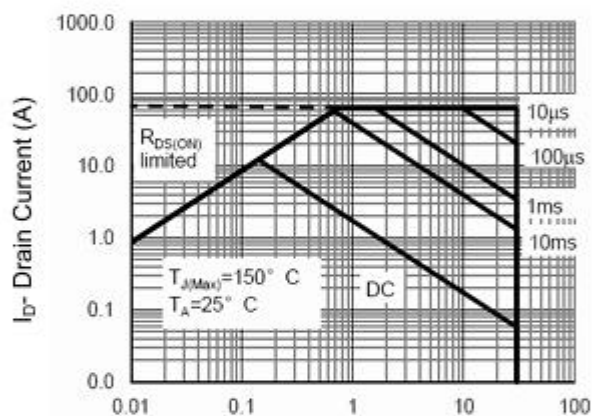
## Typical Characteristics (Cont.)



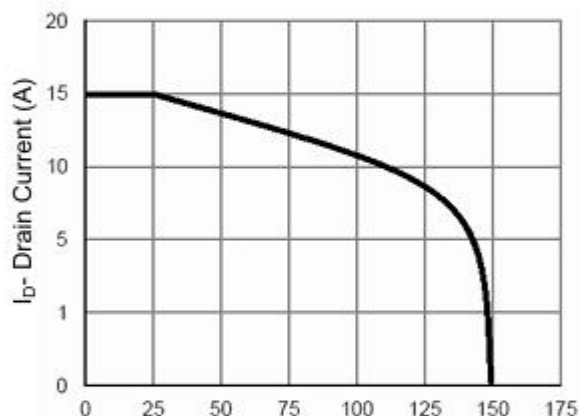
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



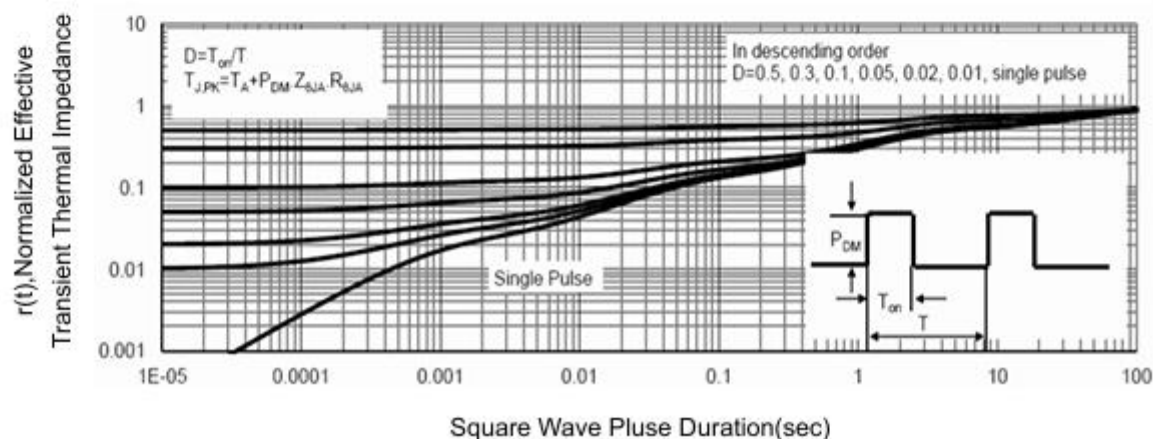
Tc-Case Temperature(°C)  
**Figure 9 Power De-rating**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**

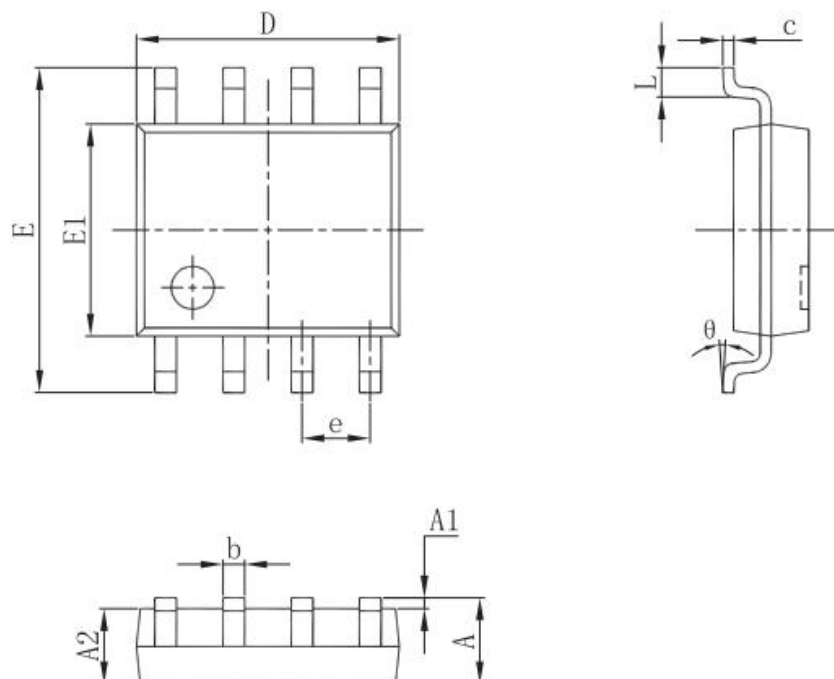


Tj-Junction Temperature(°C)  
**Figure 10 ID Current- Junction Temperature**



Square Wave Pluse Duration(sec)  
**Figure 11 Normalized Maximum Transient Thermal Impedance**

## Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



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